

### General Description

The WSD60N12GDN56 is SGT II technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

The WSD60N12GDN56 meet the RoHS and Green Product requirement, 100%  $E_{AS}$  guaranteed with full function reliability approved.

### Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent  $CdV/dt$  effect decline
- 100%  $E_{AS}$  Guaranteed
- Green Device Available

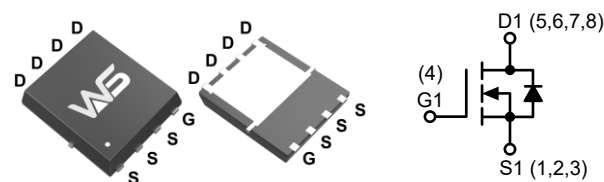
### Product Summary

$BV_{DSS}$	$R_{DS(ON)}$	$I_D$
120V	10m $\Omega$	70A

### Applications

- Mobile phone fast charging
- Brushless motor
- Home appliance control board

### DFN5X6-8L Pin Configuration



### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	120	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	
$I_D@T_C=25^\circ C$	Continuous Drain Current	70	A
$I_{DP}$	Pulsed Drain Current	150	
$E_{AS}$	Avalanche Energy, Single pulse	53.8	mJ
$P_D@T_C=25^\circ C$	Total Power Dissipation	140	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	

### Thermal Data

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	---	25	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	0.89	

**Electrical Characteristics** ( $T_J=25^{\circ}\text{C}$ , Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$ , $I_D=250\mu\text{A}$	120	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$ , $I_D=10\text{A}$	---	10	15	m $\Omega$
		$V_{GS}=4.5\text{V}$ , $I_D=10\text{A}$	---	18	25	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$ , $I_D=250\mu\text{A}$	1.2	---	2.5	V
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=80\text{V}$ , $V_{GS}=0\text{V}$ , $T_J=25^{\circ}\text{C}$	---	---	1.0	$\mu\text{A}$
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20\text{V}$ , $V_{DS}=0\text{V}$	---	---	$\pm 100$	nA
$Q_g$	Total Gate Charge (10V)	$V_{DS}=50\text{V}$ , $V_{GS}=10\text{V}$ , $I_D=25\text{A}$	---	33	---	nC
$Q_{gs}$	Gate-Source Charge		---	5.6	---	
$Q_{gd}$	Gate-Drain Charge		---	7.2	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=50\text{V}$ , $V_{GS}=10\text{V}$ , $R_G=2\Omega$ , $I_D=25\text{A}$	---	22	---	ns
$T_r$	Rise Time		---	10	---	
$T_{d(off)}$	Turn-Off Delay Time		---	85	---	
$T_f$	Fall Time		---	112	---	
$C_{iss}$	Input Capacitance	$V_{DS}=50\text{V}$ , $V_{GS}=0\text{V}$ , $f=1.0\text{MHz}$	---	2640	---	pF
$C_{oss}$	Output Capacitance		---	330	---	
$C_{rss}$	Reverse Transfer Capacitance		---	11	---	

**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
$I_S$	Continuous Source Current	$V_G=V_D=0\text{V}$ , Force Current	---	---	50	A
$I_{SP}$	Pulsed Source Current		---	---	150	
$V_{SD}$	Diode Forward Voltage	$V_{GS}=0\text{V}$ , $I_S=12\text{A}$ , $T_J=25^{\circ}\text{C}$	---	---	1.3	V
$t_{rr}$	Reverse Recovery Time	$I_F=25\text{A}$ , $di/dt=100\text{A}/\mu\text{s}$ , $T_J=25^{\circ}\text{C}$	---	62	---	ns
$Q_{rr}$	Reverse Recovery Charge		---	135	---	nC

**Note:**

1. Calculated continuous current based on maximum allowable junction temperature.
2. Repetitive rating: pulse width limited by max. junction temperature.
3.  $P_D$  is based on max. junction temperature, using junction-case thermal resistance.
4. The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^{\circ}\text{C}$ .
5.  $V_{DD}=50\text{V}$ ,  $R_G=25\Omega$ ,  $L=0.3\text{mH}$ , starting  $T_J=25^{\circ}\text{C}$ .

### Typical Characteristics

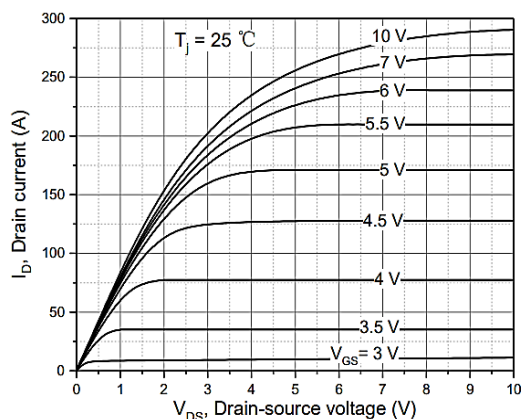


Figure 1. Typ. output characteristics

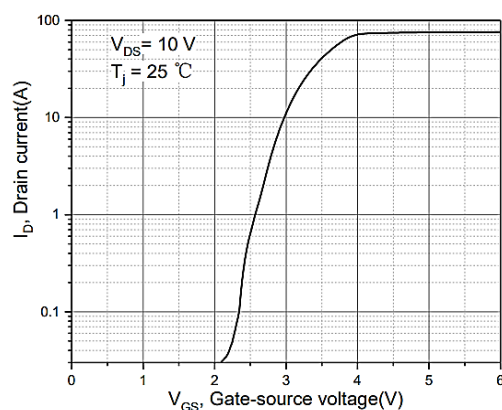


Figure 2. Typ. transfer characteristics

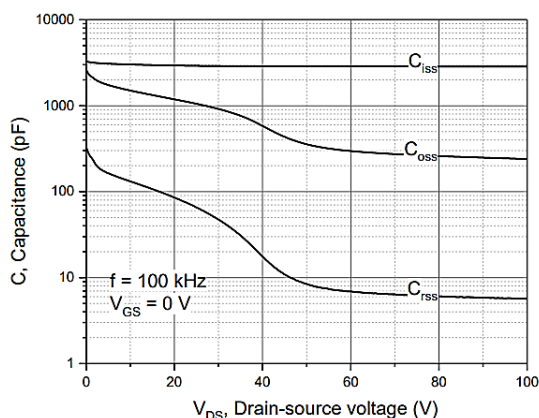


Figure 3. Typ. capacitances

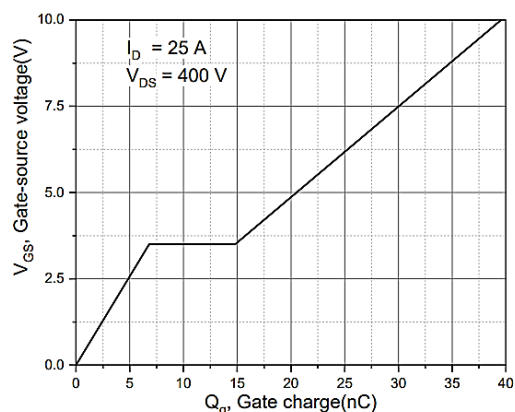


Figure 4. Typ. gate charge

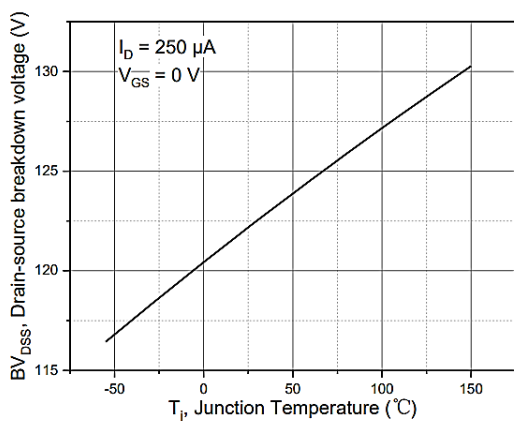


Figure 5. Drain-source breakdown voltage

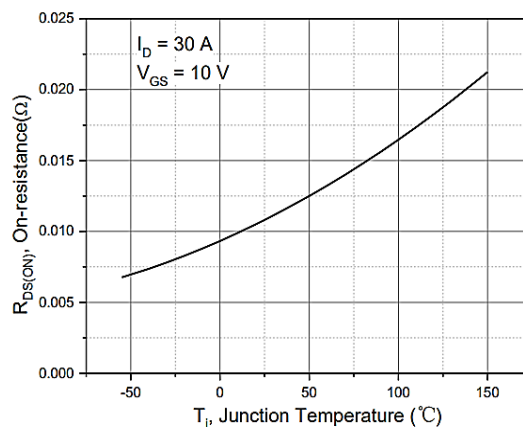


Figure 6. Drain-source on-state resistance

## Typical Characteristics (Cont.)

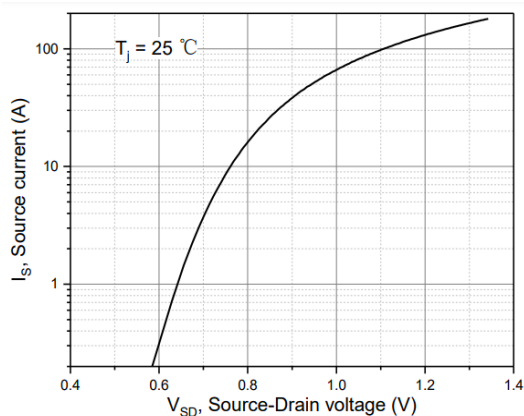


Figure 7. Forward characteristic of body diode

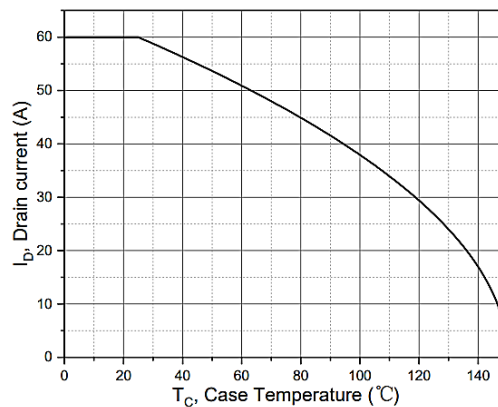


Figure 8. Drain current

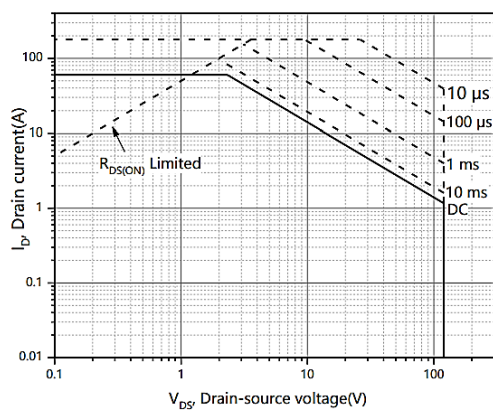
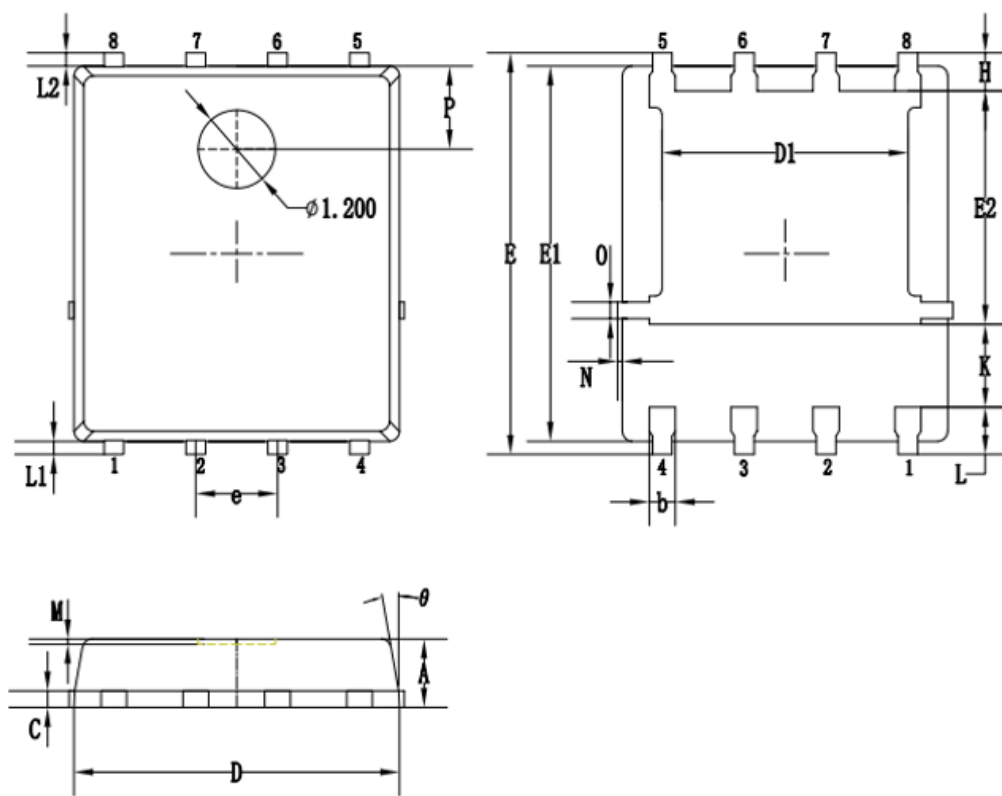


Figure 9. Safe operation area  $T_C=25\text{ }^{\circ}\text{C}$

## Packaging information



SYMBOLS	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.05	1.20
b	0.35	0.40	0.50
C	0.20	0.25	0.35
D	4.90	5.05	5.20
D1	3.72	3.82	3.92
E	6.00	6.15	6.30
E1	5.60	5.75	5.90
E2	3.47	3.57	3.67
e	1.27 BSC.		
H	0.48	0.58	0.68
K	1.17	1.27	1.37
L	0.64	0.74	0.84
L1/L2	0.20 REF.		
$\theta$	8°	10°	12°
M	0.08 REF.		
N	0	-	0.15
O	0.25 REF.		
P	1.28 REF.		

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